



#### 40V +175°C DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BVDSS	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
40V	$15m\Omega @ V_{GS} = 10V$	42A

## **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power-management functions
- DC-DC converters

#### **Features and Benefits**

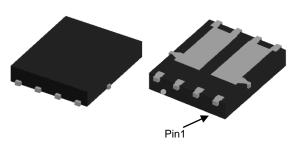
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH4011SPDQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

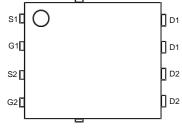
https://www.diodes.com/quality/product-definitions/

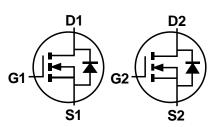
#### **Mechanical Data**

- Package: PowerDI<sup>®</sup>5060-8
- Package Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 ®3
- Weight: 0.097 grams (Approximate)

#### PowerDI5060-8 (Type C)







Top View

**Bottom View** 

Pinout Top View

**Equivalent Circuit** 

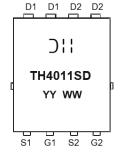
## **Ordering Information** (Note 4)

Part Number	Package	Packing		
Fait Number	Package	Qty.	Carrier	
DMTH4011SPDQ-13	PowerDI5060-8 (Type C)	2,500	Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



Office Manufacturer's Marking
TH4011SD = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 24 = 2024)
WW = Week (01 to 53)



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	40	V	
Gate-Source Voltage	Vgss	±20	V	
Continuous Drain Current (Note 6)	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I <sub>D</sub>	42 29.7	А
Continuous Drain Current (Note 5) $T_{A} = +25^{\circ}C$ $T_{A} = +100^{\circ}C$		lo	11.1 7.8	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	70	Α	
Maximum Continuous Body Diode Forward Current (Note 6)	Is	39.3	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	Isм	70	Α	
Avalanche Current, L = 0.3mH	IAS	11.9	Α	
Avalanche Energy, L = 0.3mH		Eas	21.4	mJ

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	PD	2.6	W
Thermal Resistance, Junction to Ambient (Note 5)	Reja	57	°C/W
Total Power Dissipation (Note 6)	PD	37.5	W
Thermal Resistance, Junction to Case (Note 6)	R <sub>0</sub> JC	4	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +175	°C

## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BVDSS	40	_	_	V	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μA	$V_{DS} = 32V$ , $V_{GS} = 0V$	
Gate-Source Leakage	Igss		_	±100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(th)	2	1	4	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	11.6	15	mΩ	$V_{GS} = 10V, I_D = 20A$	
Diode Forward Voltage	VsD		_	1.2	V	Vgs = 0V, Is = 20A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	805	_	pF	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss	_	208	_	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	15	_	pF		
Gate Resistance	Rg	_	2.76	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Qg	_	10.6	_	nC	V <sub>DS</sub> = 20V, I <sub>D</sub> = 20A, V <sub>GS</sub> = 10V	
Gate-Source Charge	Qgs	_	2.2	_	nC		
Gate-Drain Charge	Qgd	_	2.7	_	nC		
Turn-On Delay Time	tD(ON)	_	4.1	_	ns	$V_{DD} = 20V, V_{GS} = 10V,$ $R_{G} = 1.6\Omega, I_{D} = 20A$	
Turn-On Rise Time	t <sub>R</sub>	_	3.8	_	ns		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	8.6	_	ns		
Turn-Off Fall Time	tF	_	1.9	_	ns		
Body Diode Reverse Recovery Time	trr	_	10.2	_	ns	Ir = 15A, di/dt = 400A/μs	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	_	9.6	_	nC		

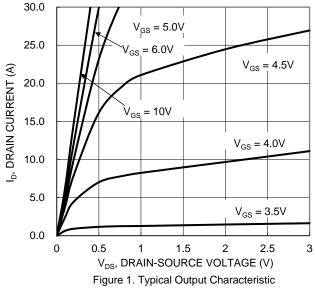
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz. copper, with thermal bias to bottom layer 1inch square copper plate.

<sup>6.</sup> Thermal resistance from junction to soldering point (on the exposed drain pad).

<sup>7.</sup> Short duration pulse test used to minimize self-heating effect.

<sup>8.</sup> Guaranteed by design. Not subject to product testing.





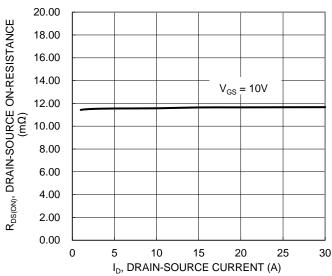


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

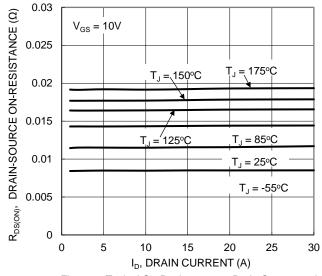


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

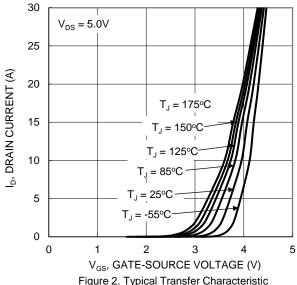


Figure 2. Typical Transfer Characteristic

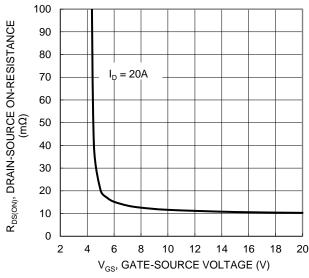


Figure 4. Typical Transfer Characteristic

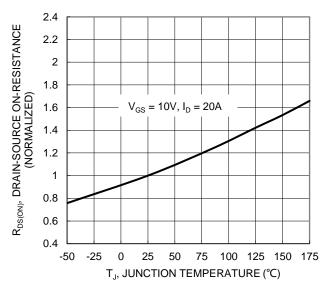


Figure 6. On-Resistance Variation with Temperature





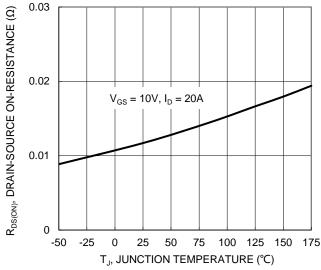
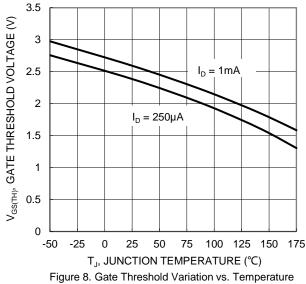


Figure 7. On-Resistance Variation with Temperature



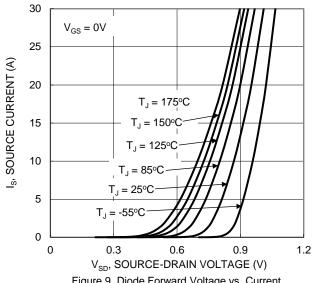
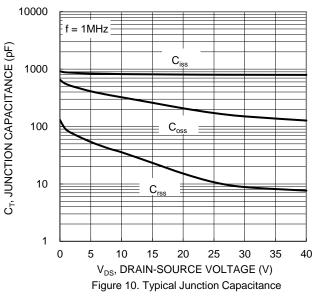


Figure 9. Diode Forward Voltage vs. Current

 $V_{DS} = 20V, I_{D} = 20A$ 

 $Q_q$  (nC)

Figure 11. Gate Charge



ID, DRAIN CURRENT (A) 12

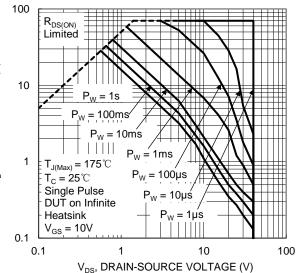


Figure 12. SOA, Safe Operation Area

2

10

8

6

4

2

0

0

 $V_{GS}(V)$ 

10



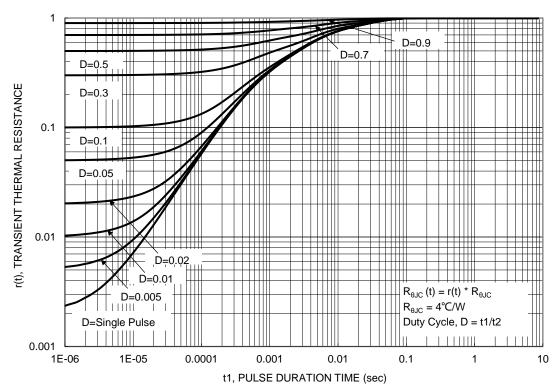


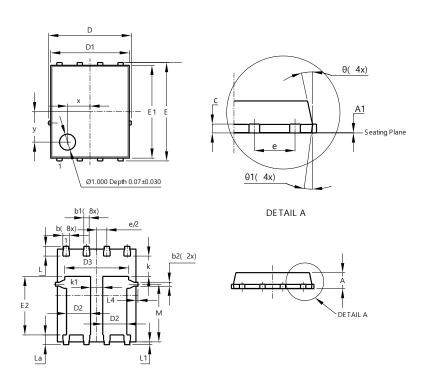
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (Type C)

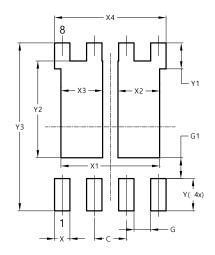


PowerDI5060-8 (Type C)				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A1	0	0.05	0.02	
b	0.33	0.51	0.41	
b1	0.300	0.366	0.333	
b2	0.20	0.35	0.25	
С	0.23	0.33	0.277	
D	5	.15 BS0		
D1	4.85	4.95	4.90	
D2	1.40	1.60	1.50	
D3	-	-	3.98	
E	6	.15 BS0		
E1	5.75	5.85	5.80	
E2	3.56	3.76	3.66	
е	1.27BSC			
k	-	-	1.27	
k1	0.56	-	-	
L	0.51	0.71	0.61	
La	0.51	0.71	0.61	
L1	0.05	0.20	0.175	
L4	-	-	0.125	
М	3.50	3.71	3.605	
х	-	-	1.400	
у	-	-	1.900	
θ	10°	12°	11°	
θ1	6°	8°	7°	
All Dimensions in mm				

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (Type C)



Dimensions	Value (in mm)			
Difficusions				
С	1.270			
G	0.660			
G1	0.820			
X	0.610			
X1	3.910			
X2	1.650			
Х3	1.650			
X4	4.420			
Υ	1.270			
Y1	1.020			
Y2	3.810			
Y3	6.610			



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